

# Muhammad Hasibul Alam

## List of Publications by Year in descending order

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Version: 2024-02-01

15  
papers

350  
citations

1684188

5  
h-index

1872680

6  
g-index

16  
all docs

16  
docs citations

16  
times ranked

609  
citing authors

#	ARTICLE	IF	CITATIONS
1	Silicene, silicene derivatives, and their device applications. Chemical Society Reviews, 2018, 47, 6370-6387.	38.1	261
2	Lithium-ion electrolytic substrates for sub-1V high-performance transition metal dichalcogenide transistors and amplifiers. Nature Communications, 2020, 11, 3203.	12.8	31
3	Disassembling Silicene from Native Substrate and Transferring onto an Arbitrary Target Substrate. Advanced Functional Materials, 2020, 30, 2004546.	14.9	21
4	Wafer-Scalable Single-Layer Amorphous Molybdenum Trioxide. ACS Nano, 2022, 16, 3756-3767.	14.6	16
5	Direct growth of $\text{MoS}_2$ on electrolytic substrate and realization of high-mobility transistors. Physical Review Materials, 2021, 5, .	2.4	12
6	Comparative analysis of subthreshold swing models for different double gate MOSFETs. , 2008, , .		4
7	In <sub>x</sub> Ga <sub>1-x</sub> Sb MOSFET: Performance analysis by self consistent CV characterization and direct tunneling gate leakage current. , 2012, , .		2
8	Effect of biaxial strain on structural and electronic properties of graphene / boron nitride hetero bi-layer structure. , 2014, , .		2
9	Electric Field Tunable Band Gap in Bi-Axially Strained Graphene/Hexagonal Boron Nitride Super-Lattice. ECS Transactions, 2015, 66, 1-10.	0.5	1
10	Self-consistent C-V characterization of depletion mode buried channel InGaAs/InAs Quantum Well FET incorporating strain effects. , 2012, , .		0
11	A physically based analytical modeling of threshold voltage control for fully-depleted SOI double gate NMOS-PMOS Flexible-FET. , 2012, , .		0
12	Self consistent simulation of C-V characterization and ballistic performance of double gate SOI flexible-FET incorporating QM effects. , 2012, , .		0
13	Physical/process parameter dependence of gate capacitance and ballistic performance of InAs <sub>y</sub> Sb <sub>1-y</sub> Quantum Well Field Effect Transistors. , 2013, , .		0
14	A Physically Based Analytical Model to Predict Quantized Eigen Energies and Wave Functions Incorporating Penetration Effect. ECS Transactions, 2014, 58, 9-15.	0.5	0
15	Performance Analysis of InAs/AlSb MOS-HEMT by Self-Consistent Capacitance-Voltage Characterization and Direct Tunneling Gate Leakage Current. ECS Transactions, 2016, 72, 189-195.	0.5	0